

### Description

The HSK6008 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

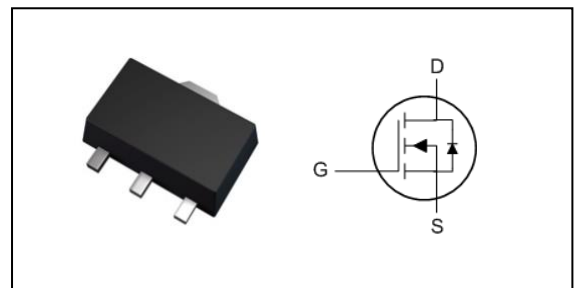
The HSK6008 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

### Product Summary

$V_{DS}$	60	V
$R_{DS(ON),typ}$	80	m $\Omega$
$I_D$	3.2	A

### SOT89 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V <sub>1</sub>	3.2	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V <sub>1</sub>	2.3	A
$I_{DM}$	Pulsed Drain Current <sub>2</sub>	12	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sub>3</sub>	1.5	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sub>1</sub>	---	85	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sub>1</sub>	---	48	$^\circ\text{C/W}$



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	---	---	V
ΔB <sub>V</sub> DSS/ΔT <sub>J</sub>	B <sub>V</sub> DSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.054	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sub>2</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.5A	---	80	100	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	---	85	110	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	---	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.96	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =2A	---	13	---	S
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =48V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	---	5	7.0	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.68	2.4	
Q <sub>gd</sub>	Gate-Drain Charge		---	1.9	2.7	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =2A	---	1.6	3.2	ns
T <sub>r</sub>	Rise Time		---	7.2	13	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	25	50	
T <sub>f</sub>	Fall Time		---	14.4	28.8	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	511	715	pF
C <sub>oss</sub>	Output Capacitance		---	38	53	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	25	35	

**Diode Characteristics**

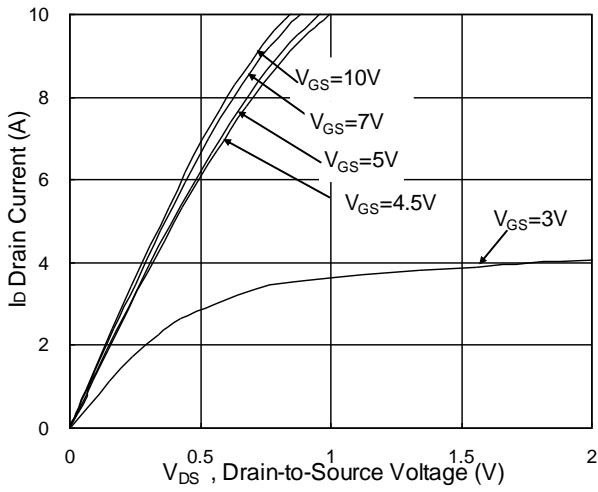
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sub>1,4</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	3.2	A
I <sub>SM</sub>	Pulsed Source Current <sub>2,4</sub>		---	---	12	A
V <sub>SD</sub>	Diode Forward Voltage <sub>2</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =2A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	9.7	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	5.8	---	nC

Note :

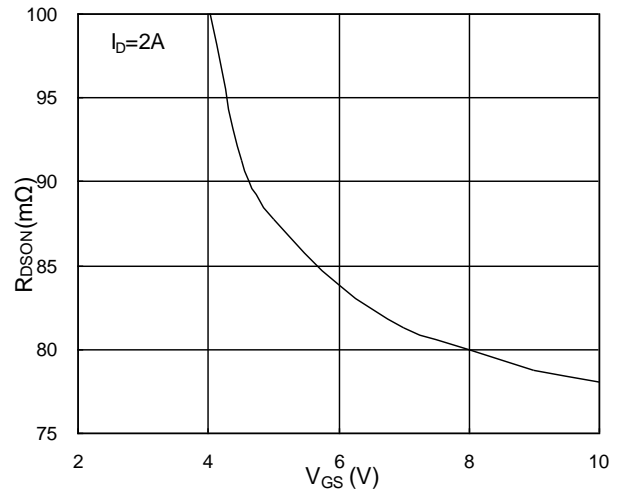
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature.
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.



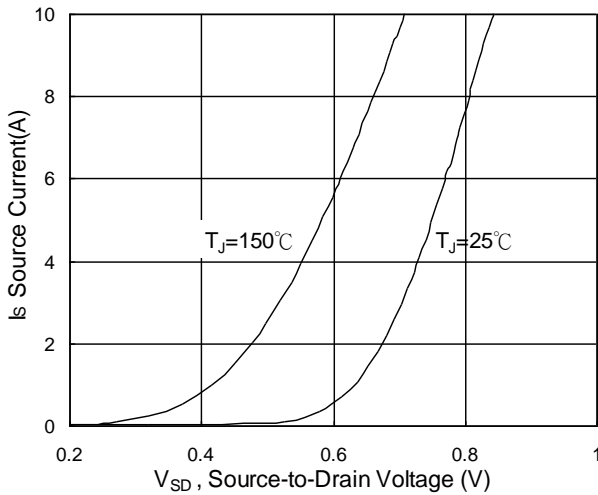
**Typical Characteristics**



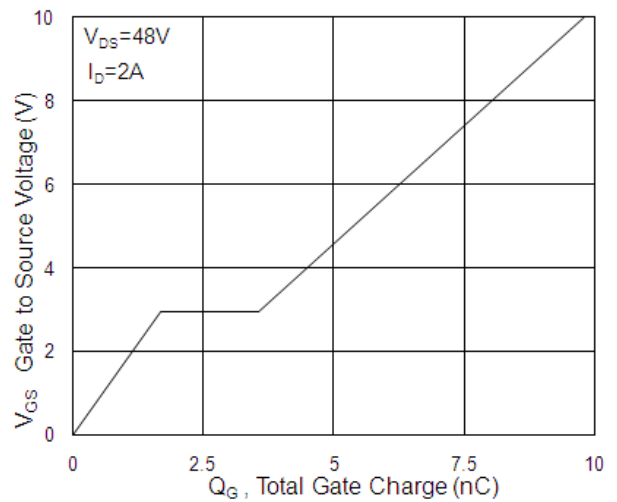
**Fig.1 Typical Output Characteristics**



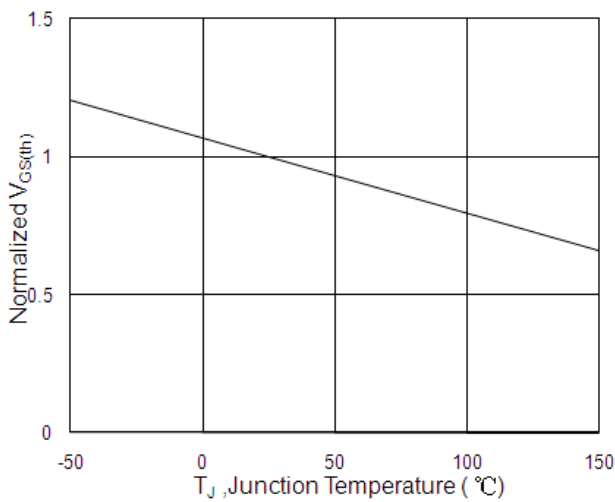
**Fig.2 On-Resistance v.s Gate-Source**



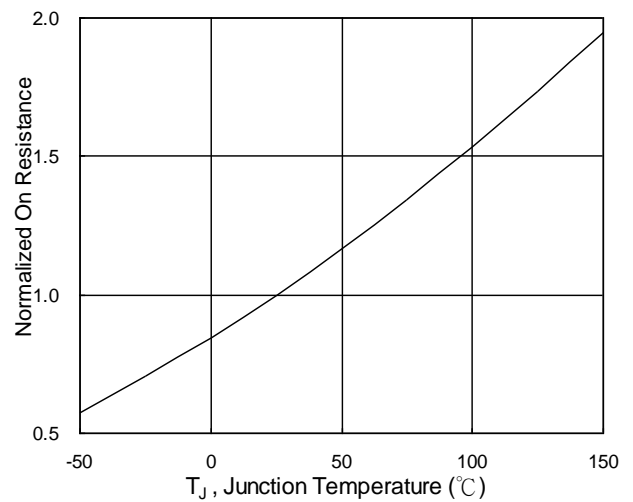
**Fig.3 Forward Characteristics of Reverse**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**

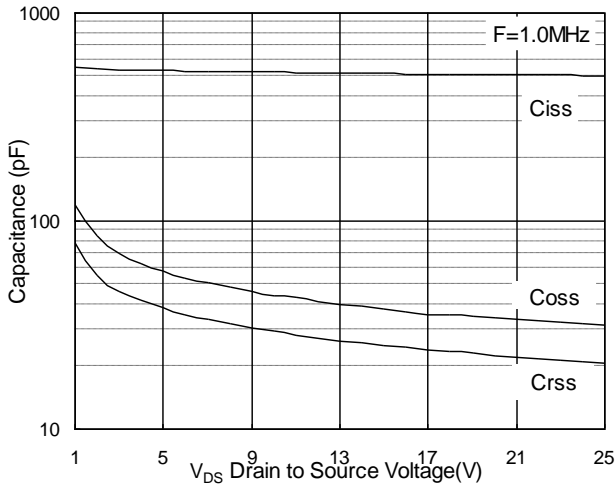


Fig.7 Capacitance

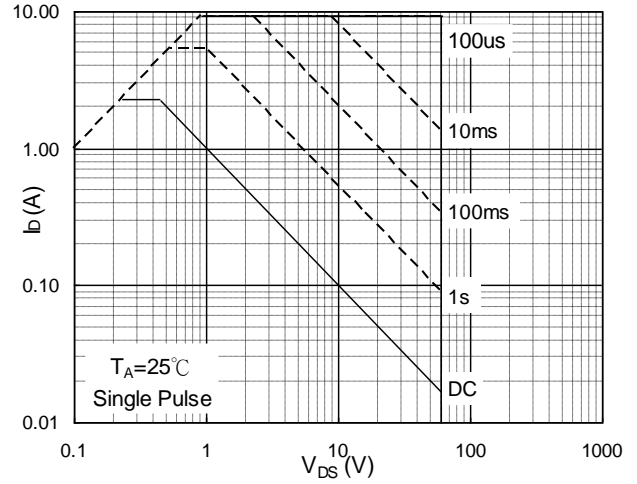


Fig.8 Safe Operating Area

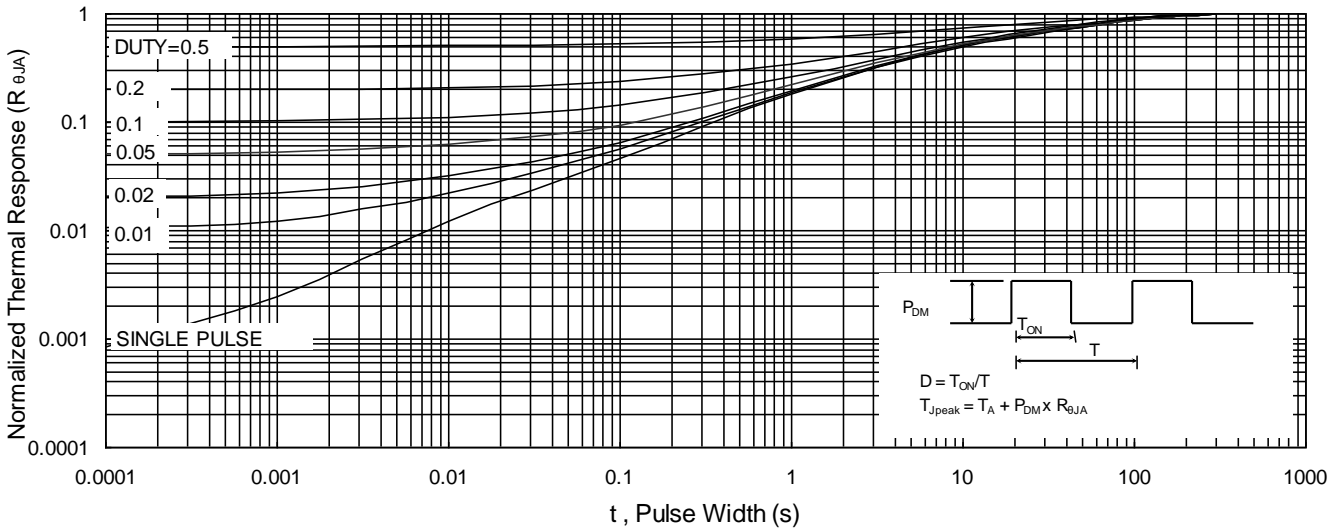


Fig.9 Normalized Maximum Transient Thermal Impedance

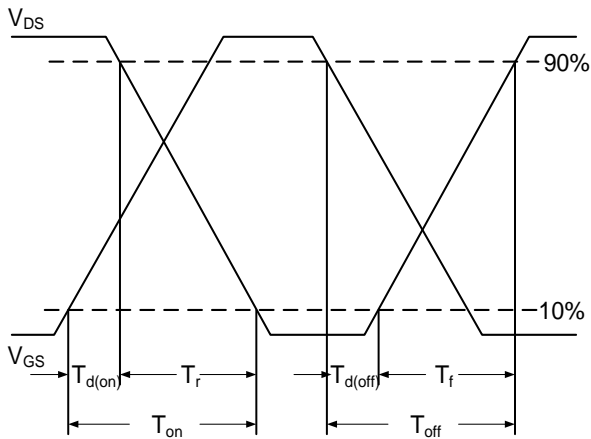


Fig.10 Switching Time Waveform

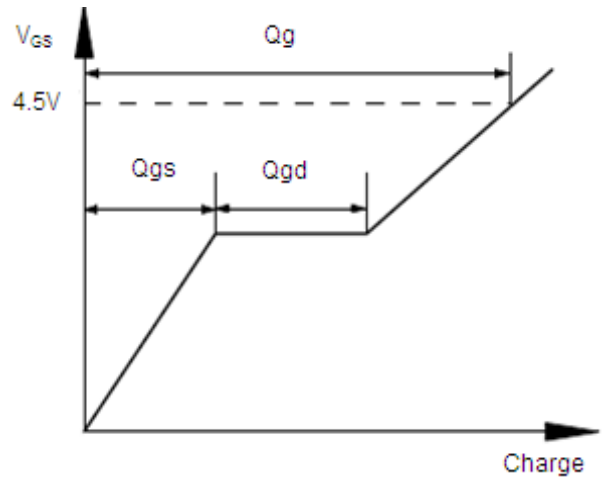
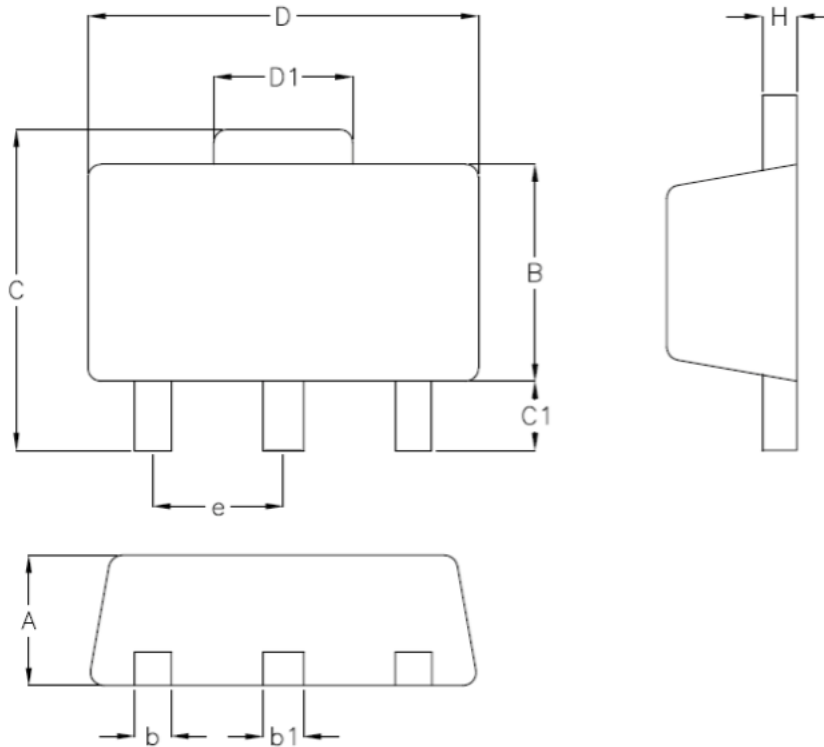


Fig.11 Gate Charge Waveform



## Ordering Information

Part Number	Package code	Packaging
HSK6008	SOT-89	4000/Tape&Reel



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.397	1.600	0.055	0.063
b	0.420	0.540	0.017	0.021
b1	0.420	0.540	0.017	0.021
B	2.388	2.591	0.094	0.102
C	3.937	4.242	0.155	0.167
C1	0.787	1.194	0.031	0.047
D	4.394	4.597	0.173	0.181
D1	1.397	1.753	0.055	0.069
e	1.448	1.549	0.057	0.061
H	0.350	0.44	0.014	0.017